

# **4V Drive Nch MOSFET**

## RP1E100XN

#### Structure

Silicon N-channel MOSFET

#### Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (MPT6).

## Application

Switching

## Packaging specifications

	Package	Taping	
Type	Code	TR	
	Basic ordering unit (pieces)	1000	
RP1E100X	0		

## ● Absolute maximum ratings (Ta = 25°C)

Parame	Symbol	Limits	Unit	
Drain-source voltage		$V_{DSS}$	30	V
Gate-source voltage		$V_{GSS}$	±20	V
Drain current	Continuous	I <sub>D</sub>	±10	Α
	Pulsed	I <sub>DP</sub> *1	±36	Α
Source current	Continuous	I <sub>S</sub>	1.6	Α
(Body Diode)	Pulsed	I <sub>SP</sub> *1	36	Α
Power dissipation		P <sub>D</sub> *2	2.0	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

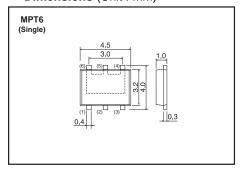
<sup>\*1</sup> Pw≤10μs, Duty cycle≤1%

### ● Thermal resistance

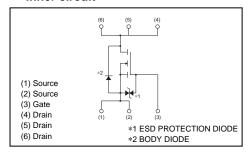
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	62.5	°C/W

<sup>\*</sup>Mounted on a ceramic board.

#### • Dimensions (Unit : mm)



#### • Inner circuit



<sup>\*2</sup> Mounted on a ceramic board.

## ● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$		-	±10	μA	$V_{GS}=\pm20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	-	-	V	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	1	-	1	μA	$V_{DS}$ =30V, $V_{GS}$ =0V
Gate threshold voltage	V <sub>GS (th)</sub>	1.0	-	2.5	V	$V_{DS}$ =10V, $I_{D}$ =1mA
	*	1	9.5	13		I <sub>D</sub> =10A, V <sub>GS</sub> =10V
Static drain-source on-state resistance	R <sub>DS (on)</sub>	1	12	17	mΩ	I <sub>D</sub> =10A, V <sub>GS</sub> =4.5V
Toolotarioo		-	13	18		I <sub>D</sub> =10A, V <sub>GS</sub> =4.0V
Forward transfer admittance	IY <sub>fs</sub> I*	8.0	-	-	S	I <sub>D</sub> =10A, V <sub>DS</sub> =10V
Input capacitance	C <sub>iss</sub>	1	800	-	pF	V <sub>DS</sub> =10V
Output capacitance	C <sub>oss</sub>	-	270	-	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	$C_{rss}$	-	140	-	pF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	-	10	-	ns	I <sub>D</sub> =5A, V <sub>DD</sub> ≒15V
Rise time	t <sub>r</sub> *	-	45	-	ns	V <sub>GS</sub> =10V
Turn-off delay time	t <sub>d(off)</sub> *	-	50	-	ns	$R_L=3.0\Omega$
Fall time	t <sub>f</sub> *	-	15	-	ns	$R_G=10\Omega$
Total gate charge	Q <sub>g</sub> *	-	11.0		nC	I <sub>D</sub> =10A, V <sub>DD</sub> ≒15V
Gate-source charge	Q <sub>gs</sub> *	-	2.4	-	nC	V <sub>GS</sub> =5V
Gate-drain charge	Q <sub>gd</sub> *	-	4.8	-	nC	

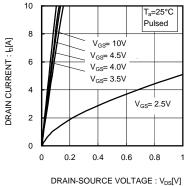
<sup>\*</sup>Pulsed

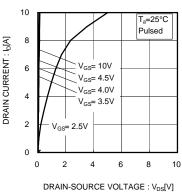
## ●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V <sub>SD</sub> *	-	-	1.2	V	I <sub>s</sub> =10A, V <sub>GS</sub> =0V

<sup>\*</sup>Pulsed

#### Electrical characteristic curves





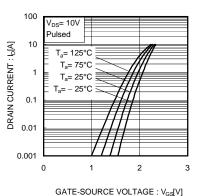
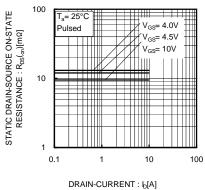


Fig.1 Typical Output Characteristics( I )

Fig.2 Typical Output Characteristics( II)

Fig.3 Typical Transfer Characteristics



STATIC DRAIN-SOURCE ON-STATE V<sub>GS</sub>= 10V Pulsed  $R_{DS}(m)[m\Omega]$ 10 RESISTANCE 1 0.1

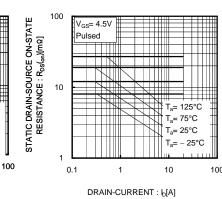


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current( I )

 $\mathsf{DRAIN}\text{-}\mathsf{CURRENT}:\mathsf{I}_\mathsf{D}\![\mathsf{A}]$ Fig.5 Static Drain-Source On-State Resistance vs. Drain Current( II )

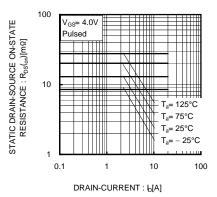
T<sub>a</sub>= 125°C

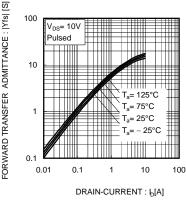
T<sub>a</sub>= 75°C

T<sub>a</sub>= 25°C

- 25°C

Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)





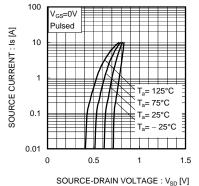


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

Fig.8 Forward Transfer Admittance vs. Drain Current

Fig.9 Reverse Drain Current vs. Sourse-Drain Voltage

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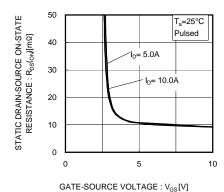


Fig.10 Static Drain-Source On-State
Resistance vs. Gate Source Voltage

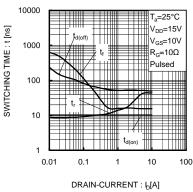


Fig.11 Switching Characteristics

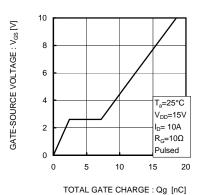


Fig.12 Dynamic Input Characteristics

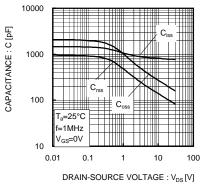
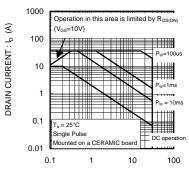


Fig.13 Typical Capacitance vs. Drain-Source Voltage



DRAIN-SOURCE VOLTAGE :  $V_{DS}[V]$ Fig.14 Maximum Safe Operating Aera

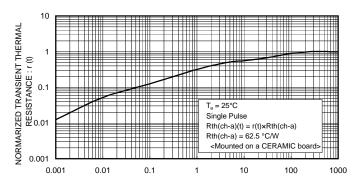


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

PULSE WIDTH : Pw(s)

## Measurement circuits

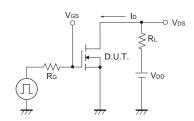


Fig.1-1 Switching time measurement circuit

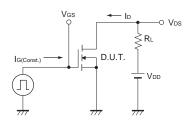


Fig.2-1 Gate charge measurement circuit

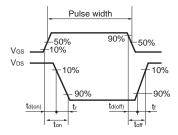


Fig.1-2 Switching waveforms

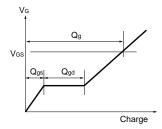


Fig.2-2 Gate Charge Waveform

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